



PTO/SB/08A (10-01)

Approved for use through 10/31/2002. OMB 0651-0031

U. S. Patent and Trademark Office: U. S. DEPARTMENT OF COMMERCE

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Substitute for form 1449A/PTO		Complete if Known			
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Application Number	10/076,486		
		Filing Date	February 19, 2002		
		First Named Inventor	Stephen L. Casper		
		Art Unit	2818		
		Examiner Name	M. Tran		
Sheet	1	of	4	Attorney Docket Number	M4065.0479/P479

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No.	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	class	sub Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (# known)				
MT	AA	6,469,364	10/2002	Kozicki	257	529
	AB	2002/0168820 App.	11/2002	Kozicki		
	AC	2000/0072188 App.	6/2002	Gilton		
	AD	2002/0123169 App.	9/2002	Moore et al.		
	AE	2002/0123248 App.	9/2002	Moore et al.		
	AF	3,622,319	11/1971	Sharp	430	396
MT	AG	3,743,847	7/1973	Boland	250	505.1
	AH	4,269,935	5/1981	Masters et al.	430	323
	AI	4,312,938	1/1982	Drexler, et al.	430	496
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	AK	4,320,191	3/1982	Yoshikawa et al.	430	296
	AL	4,405,710	9/1983	Balasubramanyam et al.	430	311
	AM	4,419,421	12/1983	Wichelhaus, et al.	429	323
	AN	4,795,657	1/1989	Formigoni et al.	427	96
MT	AO	4,847,674	7/1989	Sliwa et al.	257	767
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	AQ	5,177,567	1/1993	Klersy et al.	257	4
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	AT	5,315,131	5/1994	Kishimoto et al.	257	57
	AU	5,350,484	9/1994	Gardner et al.	438	669
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MT	AW	5,512,328	4/1996	Yoshimura et al.	427	498
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MT	AM1	6,329,606	12/2001	Freyman et al.	174	260
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				First Named Inventor	Stephen L. Casper
				Art Unit	2818
				Examiner Name	M. Tran
Sheet	2	of	4	Attorney Docket Number	M4065.0479/P479

AT	AU1	2002/0190350 APP	12/19/2002	Kozicki		
	AV1	2003/0027416 APP	2/6/2003	Moore		
	AV1	2003/0001229 APP	1/2/2003	Moore et al.		
	AX1	2002/0106849 APP	8/8/2002	Moore		
	AY1	2002/0127886 APP	9/12/2002	Moore et al.		
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	BG1	2003/0035315	02/20/03	Kozicki		
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	BI1	5,883,827	3/16/99	Morgan	365	100
BT	BJ1	4,112,512	9/5/78	Arzubi et al.	365	149

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FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No.†	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T [‡]
		Country Code ² -Number ⁴ -Kind Code ⁵ (if known)				
My	BA	JP 56126916	10/1981	Akira et al.		
	BB					

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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

† Applicant's unique citation designation number (optional). † See attached Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901:04. ‡ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). † For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the application number of the patent document. † Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. † Applicant is to place a check mark here if English language Translation is attached.

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Sheet	4	of	4	Attorney Docket Number	M4065.0479/P479

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
AY	CA	Axon Technologies Corporation, TECHNOLOGY DESCRIPTION: <i>Programmable Metalization Cell(PMC)</i> , pp 1-6 (Pre-May 2000).	
	CB	Heibert et al., <i>Intralayer hybrid resist process with submicron capability</i> SPIE Vol. 333 SUBMICRON LITHOGRAPHY, pp. 24-29 (1982).	
	CC	Hilt, DISSERTATION: <i>Materials characterization of Silver Chalcogenide Programmable Metalization Cells</i> , Arizona State University, pp Title page-114 (UMI Company, May 1999).	
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	CE	Holmquist et al., <i>Reaction and Diffusion in Silver-Arsenic Chalcogenide Glass Systems</i> , 62 J. AMER. CERAM. SOC., No. 3-4, pp. 183-188 (March-April 1979).	
	CF	Huggelt et al., <i>Development of silver sensitized germanium selenide photoresist by reactive sputter etching in SF₆</i> , 42 APPL. PHYS. LETT., No. 7, pp. 592-594 (April 1983).	
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	CJ	Kozicki, et al., <i>Nanoscale effects in devices based on chalcogenide solid solutions</i> , Superlattices and Microstructures, 27, 485-488 (2000).	
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	CP	Michael N. Kozicki, <i>1. Programmable Metalization Cell Technology Description</i> , February 18, 2000	
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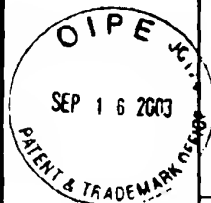
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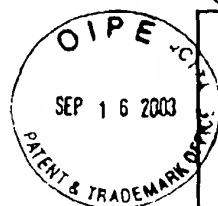
U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Document Number		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)				
AS	AA	6,388,324		05/14/2002	Kozicki et al.	257 750
	AB	US 2002/0000666		01/03/2002	Kozicki et al.	250 377
	AC	5,500,532		03/19/1996	Kozicki et al.	260 374
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	AE	5,751,012		05/12/1998	Wolstenholme et al.	257 5
	AF	5,789,277		08/04/1998	Zahorik et al.	438 95
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		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)					
AS	BA	WO 02/21542		03/14/2002	Kozicki et al.		
	BB	WO 00/48196		08/17/2000	Kozicki et al.		
AS	BC	WO 97/48032		12/18/1997	Kozicki et al.		
	BD	WO 99/28914		06/10/1999	Kozicki et al.		

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PTO/SB/088 (10-01)
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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published	T ²
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	CJ	Asahara, Y.; Izumitani, T., Voltage controlled switching in Cu-As-Se compositions, J. Non-Cryst. Solids 11 (1972) 97-104.	
AS	CK	Asokan, S.; Prasad, M.V.N.; Parthasarathy, G.; Gopal, E.S.R., Mechanical and chemical thresholds in IV-VI chalcogenide glasses, Phys. Rev. Lett. 62 (1989) 808-810	
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Sheet	3	of	8
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		Glasses, Asian Journal of Physics (2000) 9, 709-72.
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Application Number	10/076,486
Filing Date	February 19, 2002
First Named Inventor	Stephen L. Casper
Group Art Unit	2818
Examiner Name	Not Known
Attorney Docket Number	M4065.0479/P479

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U. S. PATENT DOCUMENTS						
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		Number-Kind Code ² (if known)				
DS	AA	5,761,115	06/1998	Kozicki et al.	365	182
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